

region so as to be spaced apart from, and to surround, the drain region;

a source region of the second conductivity type, which is defined in the body region;

a gate insulating film deposited over the body region;

a gate electrode formed on the gate insulating film;

a field insulating film deposited over a part of the semiconductor region, the part being located between the body and drain regions;

Q2 a metal electrode electrically connected to the drain region;

a plurality of electrically floating plate electrodes, which are spaced apart from, and surround, the drain region when the device is viewed from over the substrate; and

an interlevel dielectric film formed over the gate insulating film, the field insulating film and the floating plate electrodes,

wherein parts of the metal electrode are extended onto the interlevel dielectric film and are located over the floating plate electrodes, and

wherein each said part of the metal electrode is capacitively coupled to an associated one of the floating plate electrodes.

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